

JIEJIE MICROELECTRONICS CO., LTD.

TEL

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|--|----------|-----|----|
| Peak gate power | P_{GM} | 5 | W |
| Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7) | V_{pp} | 0.5 | kV |

NOTE 1: Operating junction temperature T_j is up to 125 when a resistor 1k is connected between Gate and Cathode. Without this resistor, the T_j is up to 110 only.

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

| Symbol | Test Condition | Value | Unit |
|--------|----------------|-------|------|
|--------|----------------|-------|------|

ORDERING INFORMATION

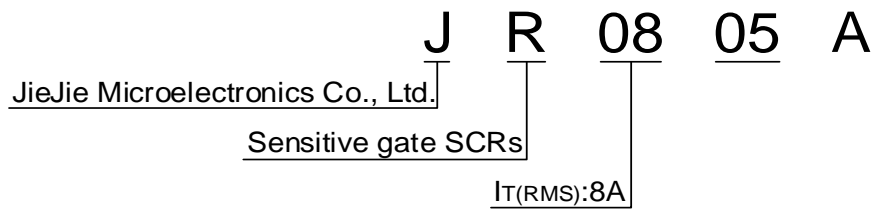


FIG.1: Maximum power dissipation versus RMS on-state current

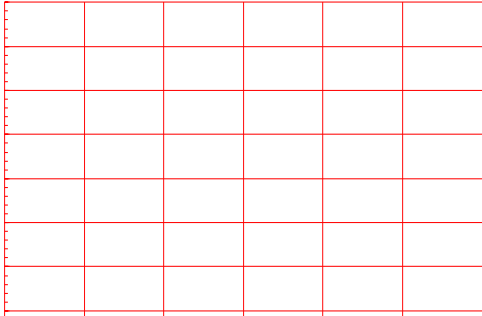
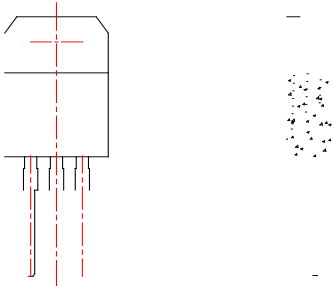


FIG.2: RMS on-state current versus case temperature

PACKAGE MECHANICAL DATA



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